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1. (Amended) A low impedance band-gap reference circuit, comprising:
a band-gap reference circuit;
a buffer circuit electronically coupled with said band-gap reference circuit; and
a voltage pull-up device electronically coupled with said band-gap reference circuit
and said buffer circuit, wherein said voltage pull-up device acts to reduce a required
supply voltage to maintain a band-gap reference voltage and wherein said voltage pull-up
device is implemented as a transistor with less than 1.0 VBE.

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7. (Amended) An electronic device, comprising:
a silicon substrate;
electronic circuitry constructed in said silicon substrate; and
a band-gap reference circuit electronically coupled in said electronic device,
wherein said electronic circuitry requires reference to the output voltage of said band-gap
reference circuit and said band-gap reference circuit is enabled for low impedance by a
buffer circuit comprising a transistor with less than 1.0 VBE.

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(Amended) An electronic device as described in Claim 7, wherein said transistor with less
than 1.0 VBE is connected as an emitter follower.

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16. (Amended) In an electronic device, a method for providing a reference voltage, comprising:
flowing current through an electronic element such that the band-gap voltage of said
electronic element provides said reference voltage;
providing a buffer circuit enabled to provide low impedance; and
adjusting the voltage across said buffer circuit so that said band-gap reference
voltage is maintained, wherein said voltage is a VBE OF LESS THAN 1.0 V.